

# GSDSRB751V-40

## Schottky Barrier Diode

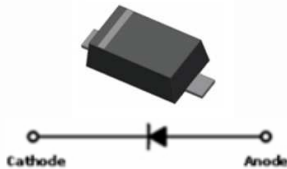
### Product Description

Schottky Barrier Diode 200mW / 30V

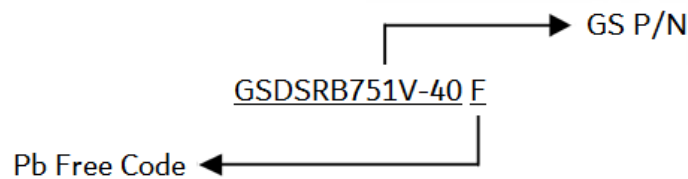
### Features

- Low Forward Voltage Drop
- Flat Lead SOD-323 Small Outline Plastic Package
- Surface Device Type Mounting
- RoHS Compliant
- Green EMC
- Matte Tin(Sn) Lead Finish
- Band Indicate Cathode

### Marking Information

Part Number	Package	Part Marking	Equivalent Circuit diagram
GSDSRB751V-40F	SOD-323	B5	

### Ordering Information



Part Number	Package	Quantity
GSDSRB751V-40F	SOD-323	3000 PCS

## Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Symbol	Parameter	Value	Unit
P <sub>D</sub>	Power Dissipation	200	mW
V <sub>RRM</sub>	Repetitive Peak Reverse Voltage	40	V
V <sub>R</sub>	Reverse Voltage	30	V
T <sub>J</sub>	Operating Junction Temperature	+125	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to +125	°C
I <sub>F</sub>	Forward Current	30	mA
I <sub>FSM</sub>	Non-Repetitive Peak Forward Current ( at 8.3ms single half sine-wave )	200	mA

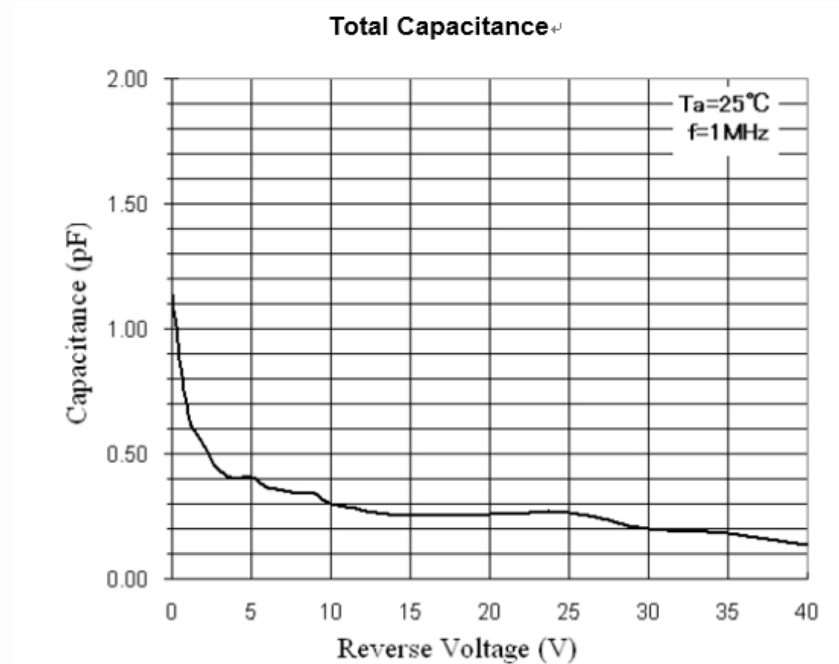
These ratings are limiting values above which the serviceability of the diode may be impaired.

## Electrical Characteristics

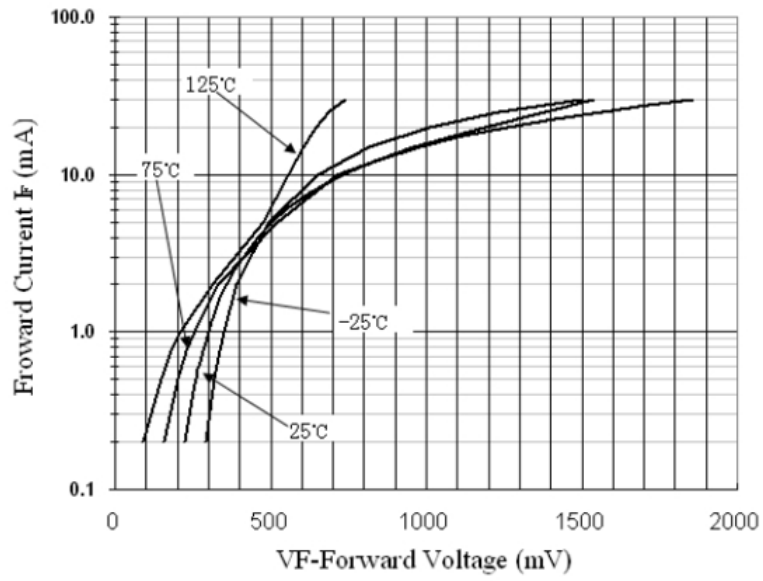
(T<sub>A</sub>=25°C Unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Max	Unit
B <sub>V</sub>	Breakdown Voltage	I <sub>R</sub> = 10μA	30	-	V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 30V	-	0.5	μA
V <sub>F</sub>	Forward Voltage	I <sub>F</sub> = 1mA	-	0.37	V

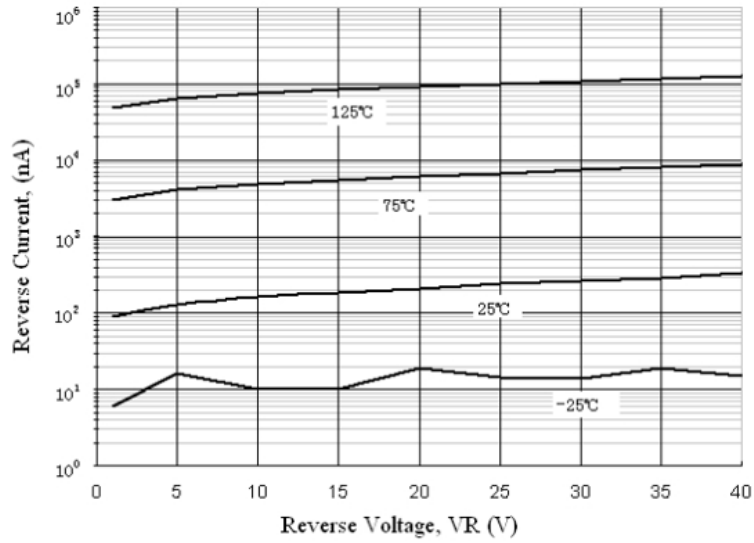
## Typical Characteristics



Forward Voltage vs Ambient Temperature

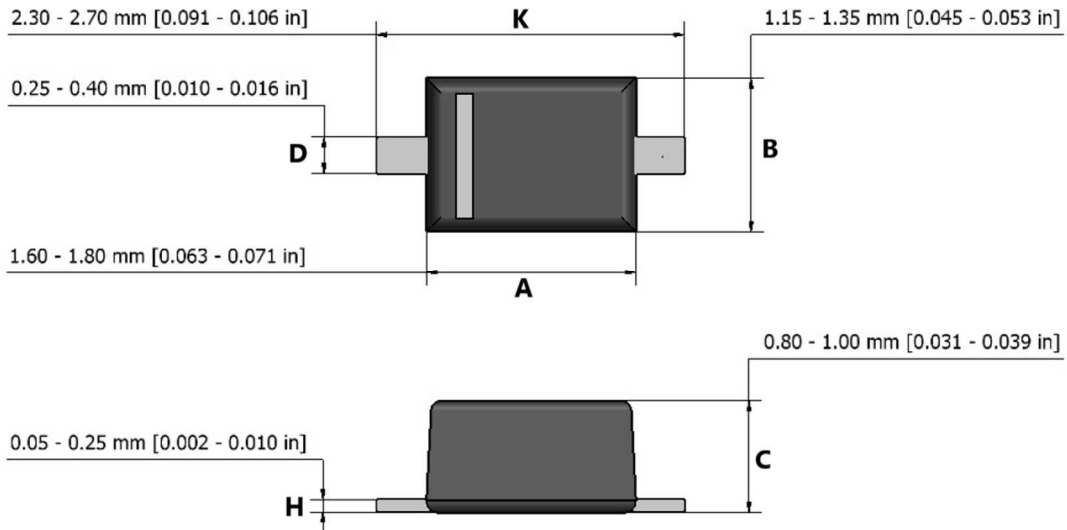


Reverse Current vs Reverse Voltage



## Package Dimension

### SOD-323



**NOTES:**

1. The above package outline is similar to JEITA SC-90.
2. Dimensions are exclusive of Burrs, Mold Flash & Tie Bar extrusions.





Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
<b>A</b>	1.6	1.8	0.063	0.071
<b>B</b>	1.15	1.35	0.045	0.053
<b>C</b>	0.8	1	0.031	0.039
<b>D</b>	0.25	0.4	0.01	0.016
<b>H</b>	0.05	0.25	0.002	0.01
<b>K</b>	2.3	2.7	0.091	0.106



Pin 1.CATHODE  
Pin 2.ANODE

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